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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/081,818
	Filing Date	February 20, 2002
	First Named Inventor	Eldridge, Jerome
	Group Art Unit	2818
	Examiner Name	Ho, Tu-Tu
Sheet 1 of 1		Attorney Docket No: 1303.045US1

US PATENT DOCUMENTS				
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
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↓	US-20060186458A1	08/24/2006	Forbes, L., et al.	02/23/2005
↓	US-4,510,584	04/09/1985	Dias, D. R., et al.	12/29/1982
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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T*

OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T*
TH		"ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS", <u>US Application Serial No 10/379470 (1303.090US1) filed March 4, 2003,</u>		
↓		"COBALT TITANIUM OXIDE DIELECTRIC FILMS", <u>US Application Serial No. 11/216958 (Attorney Docket No 1303.150US1), filed August 31, 2005,</u>		
↓		"MAGNESIUM TITANIUM OXIDE FILMS", <u>US Application Serial No 11/89075 (Attorney Docket No. 1303.148US1) filed July 25, 2005,</u>		
↓		AHN, "ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS", <u>US Application Serial No 10/379470 (1303.090US1),</u>		
↓		AHN, "CONDUCTIVE NANOPARTICLES", <u>US Application Serial No 11/197,184 (Attmy Docket No.303.904US1), filed August 4, 2005,</u>		
↓		AHN, "IRIDIUM / ZIRCONIUM OXIDE STRUCTURE", <u>US Application Serial No 11/152759 (Attmy Docket No. 1303.144US1) filed June 14, 2005,</u>		
↓		AHN, KIE Y., "LANTHANIDE YTTRIUM ALUMINUM OXIDE DIELECTRIC FILMS", <u>U.S. Application Serial No. 11/297,567, filed December 8, 2005 (Attorney Docket 1303.157US1), 05-0711,</u>		
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EXAMINER

/Tu Tu Ho/ (12/15/2006)

DATE CONSIDERED 12/15/2006

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 808. Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant. Applicant's unique citation designation number (optional) * Applicant is to place a check mark here if English language Translation is attached